

N-channel LFPAK 60 V, 11.1 m $\Omega$  standard level MOSFET

Rev. 01 — 5 January 2010

**Product data sheet** 

## 1. Product profile

### **1.1 General description**

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

### **1.3 Applications**

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### 1.4 Quick reference data

#### Table 1. Quick reference

- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

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- Motor control
- Server power supplies

	Quion reference					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	59	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	89	W
Т <sub>ј</sub>	junction temperature		-55	-	175	°C
Avalanch	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy		-	-	71	mJ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A};$	-	6.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{\text{DS}}$ = 30 V; see <u>Figure 14</u> and <u>15</u>	-	28.4	-	nC

Table 1.	Quick reference	.continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static c	haracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	17.8	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ see Figure 13	-	8	11.1	mΩ

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate	q	
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

# 3. Ordering information

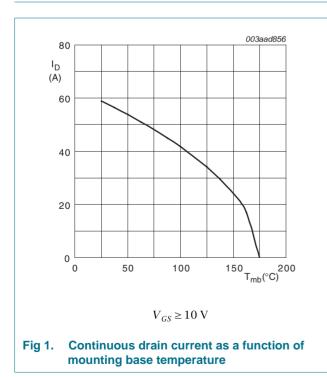
Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PSMN012-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669	

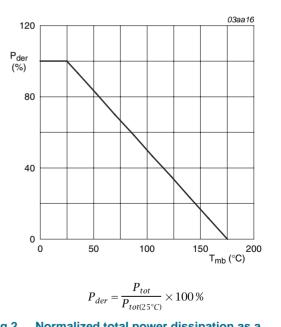
## 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	42	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	59	А
I <sub>DM</sub>	peak drain current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	236	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	89	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-dr	ain diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	59	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	236	А
Avalanche	e ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 59 A; $V_{sup}$ $\leq$ 60 V; $R_{GS}$ = 50 $\Omega$	-	71	mJ

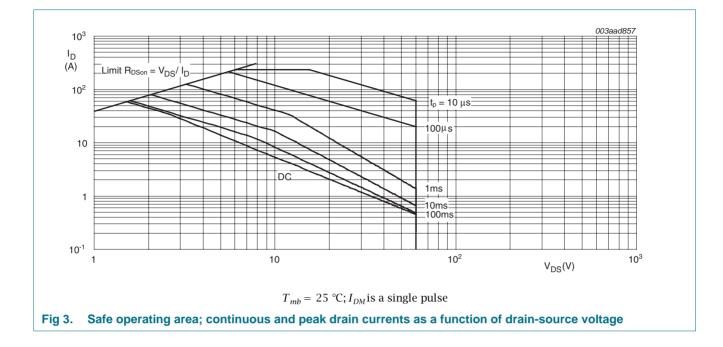






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# 5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.8	1.68	K/W



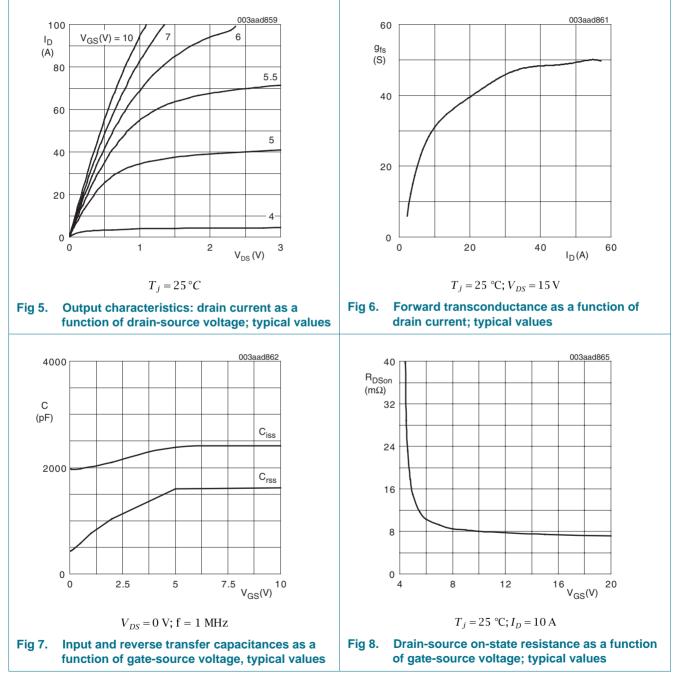
# 6. Characteristics

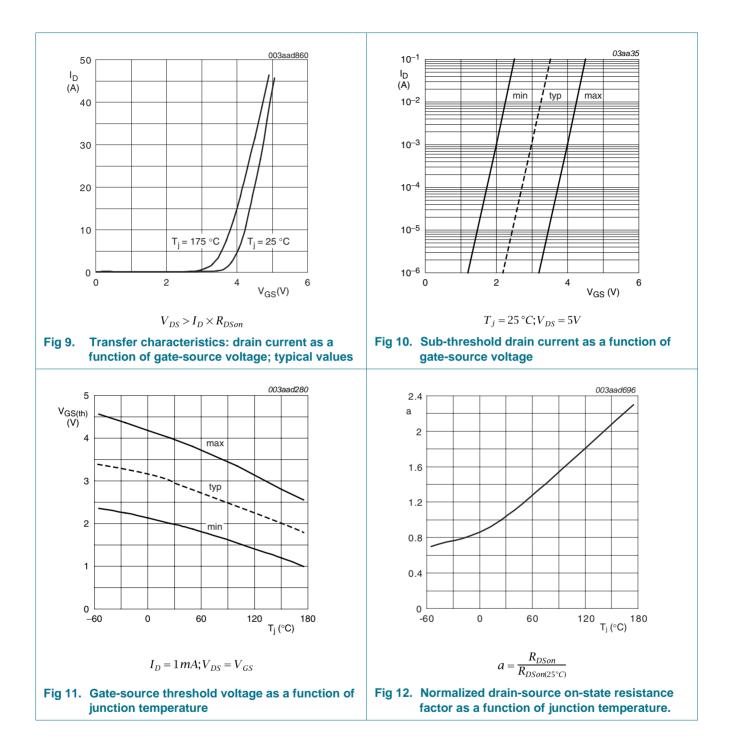
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	54	-	-	V
	breakdown voltage	$I_D$ = 250 $\mu A;~V_{GS}$ = 0 V; $T_j$ = 25 °C	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V <sub>GSth</sub>		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{1}$	-	-	4.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	0.95	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	2	μA
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R <sub>DSon</sub> drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>	-	17	25.5	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	17.8	mΩ
		$V_{GS}$ = 10 V; $I_{D}$ = 15 A; $T_{j}$ = 25 °C; see <u>Figure 13</u>	-	8	11.1	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.66	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	28.4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	23.3	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	8.75	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D$ = 30 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see Figure 14	-	4.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	3.9	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 30 A; $V_{DS}$ = 30 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> and <u>15</u>	-	6.4	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$V_{DS} = 30$ V; see <u>Figure 14</u> and <u>15</u>	-	4.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C;	-	1685	-	pF
C <sub>oss</sub>	output capacitance	see Figure 16	-	245	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	140	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	15.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	12.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	28.7	-	ns
t <sub>f</sub>	fall time		-	8.2	-	ns

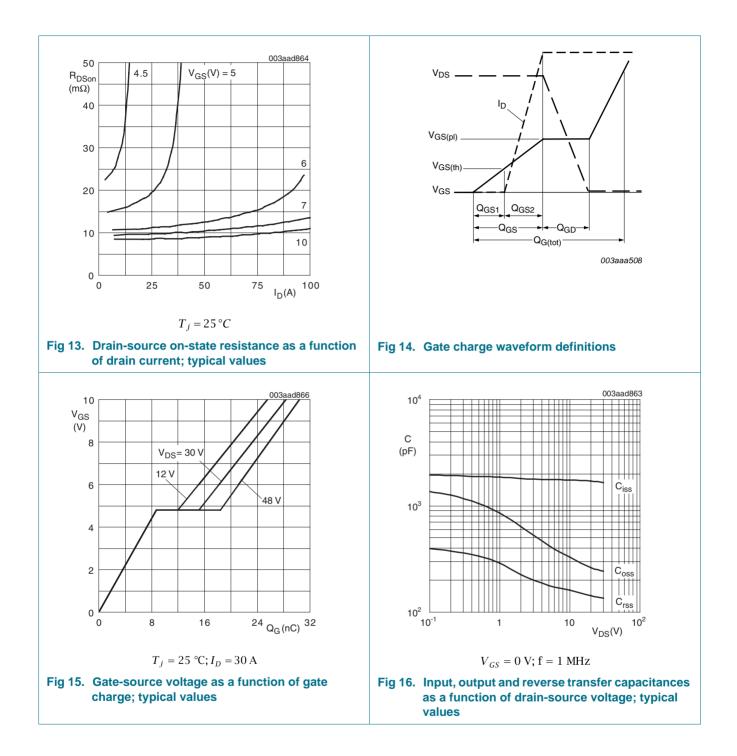
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# **PSMN012-60YS**

Table 6.	Characteristics continued							
Symbol	Parameter	Parameter Conditions				Unit		
Source-drain diode								
$V_{SD}$	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 17</u>	-	0.82	1.2	V		
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	35	-	ns		
Qr	recovered charge	$V_{DS} = 30 V$	-	41	-	nC		

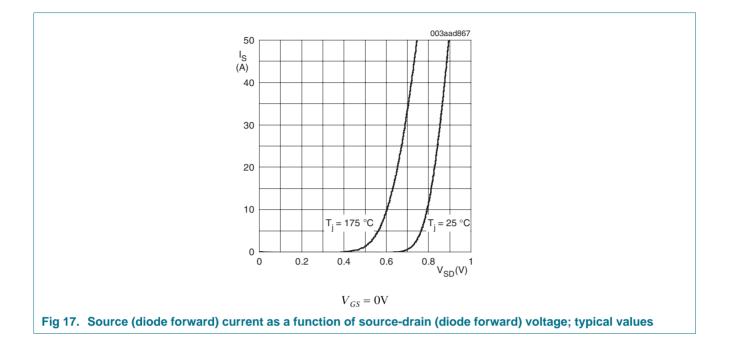






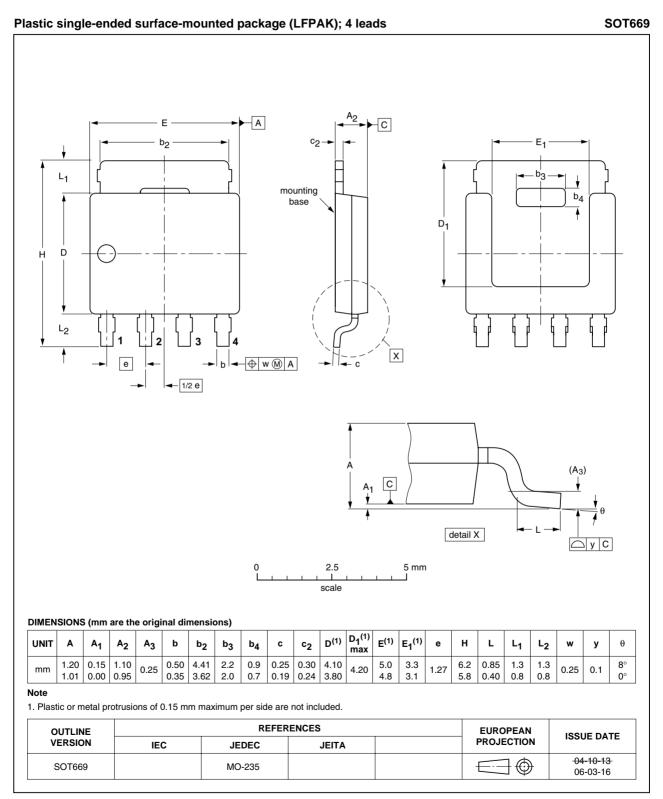
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# **PSMN012-60YS**



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## 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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# 8. Revision history

Table 7. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN012-60YS_1	20100105	Product data sheet	-	-

# 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions"

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